TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor
SCHS022

CD4011UB Types

CMOS Quad 2-Input NAND Gate

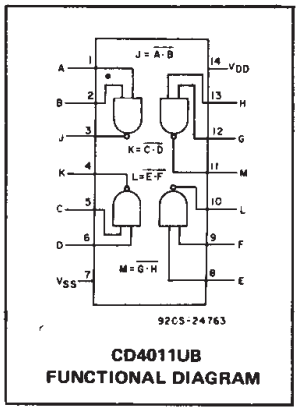
High-Voltage Types (20-Volt Rating)

■ CD4011UB quad 2-input NAND gate provides the system designer with direct implementation of the NAND function and supplements the existing family of CMOS gates.

The CD4011UB types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

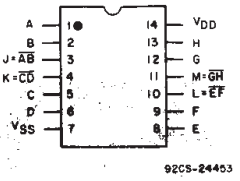
Features:

- Propagation delay time = 30 ns (typ). at C_L = 50 pF, V_{DD} = 10 V
- Standardized symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package temperature range; 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative **Standard No. 13B, "Standard Specifications** for Description of 'B' Series CMOS Devices"



CD4011UB
FUNCTIONAL DIAGRAM

TERMINAL ASSIGNMENT



TOP VIEW

CD4011UB

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
Voltages referenced to V_{SS} Terminal) ..... -0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -55°C to +100°C 500mW
For T_A = +100°C to +125°C ..... Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) 100mW
OPERATING-TEMPERATURE RANGE (T_A) ..... -55°C to +125°C
STORAGE TEMPERATURE RANGE (T_{stg}) ..... -65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max ..... +265°C

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges.

CHARACTERISTIC	MIN.	MAX.	UNITS
Supply Voltage Range (For T_A = Full Package Temperature Range)	3	18	V

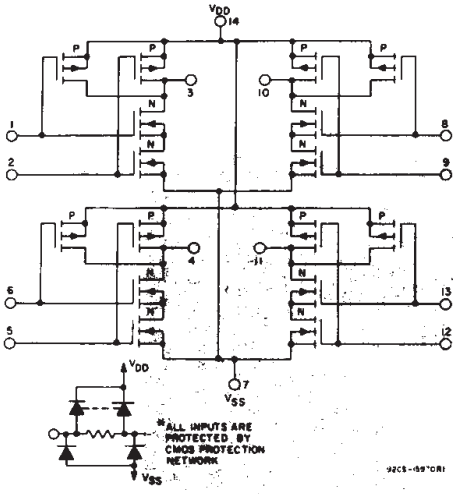


Fig. 1 – Schematic diagram for type CD4011UB.

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
								+25			
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	0.25	0.25	7.5	7.5	–	0.01	0.25	μA
	–	0,10	10	0.5	0.5	15	15	–	0.01	0.5	
	–	0,15	15	1	1	30	30	–	0.01	1	
	–	0,20	20	5	5	150	150	–	0.02	5	
Output Low (Sink) Current I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0,5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	–	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	–	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage, V_{IL} Max.	4.5	–	5	1				—	—	1	V
	9	–	10	2				—	—	2	
	13.5	–	15	2.5				—	—	2.5	
Input High Voltage, V_{IH} Min.	0.5,4.5	–	5	4				4	—	—	
	1,9	–	10	8				8	—	—	
	1.5,13.5	–	15	12.5				12.5	—	—	
Input Current I_{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	–	$\pm 10^{-5}$	±0.1	μA

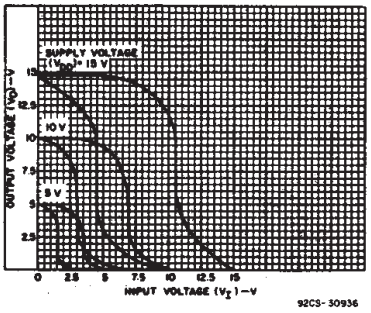


Fig. 2 – Minimum and maximum voltage transfer characteristics.

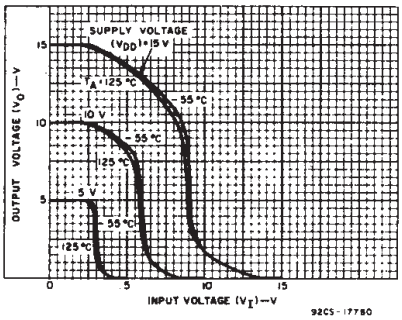


Fig. 3 – Typical voltage transfer characteristics as a function of temperature.

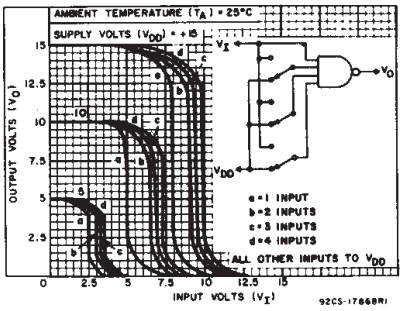


Fig. 4 – Typical multiple input switching transfer characteristics for CD4012UB.

DYNAMIC ELECTRICAL CHARACTERISTICS

At T_A = 25°C, Input t_r, t_f = 20 ns, and C_L = 50 pF, R_L = 200kΩ

CHARACTERISTIC	TEST CONDITIONS	LIMITS		UNITS
	V_{DD} VOLTS	TYP.	MAX	
Propagation Delay Time, t_{PHL}, t_{PLH}	5	60	120	ns
	10	30	60	
	15	25	50	
Transition Time, t_{THL}, t_{TLH}	5	100	200	ns
	10	50	100	
	15	40	80	
Input Capacitance, C_{IN}	Any Input	10	15	pF

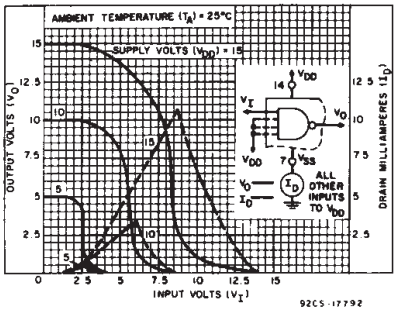


Fig. 5 – Typical current and voltage transfer characteristics.

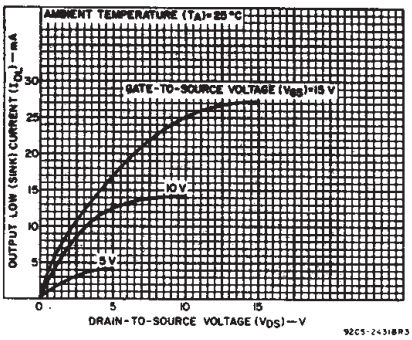


Fig. 6 – Typical output low (sink) current characteristics.

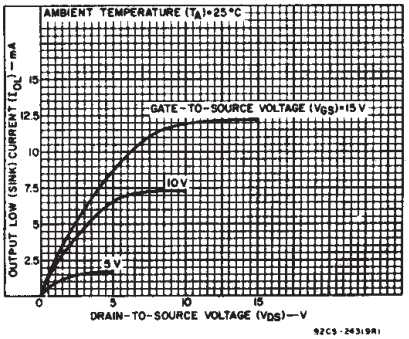


Fig. 7 – Minimum output low (sink) current characteristics.

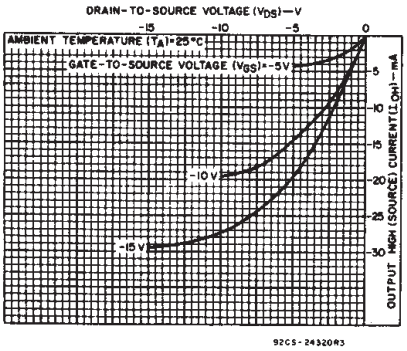


Fig. 8 – Typical output high (source) current characteristics.

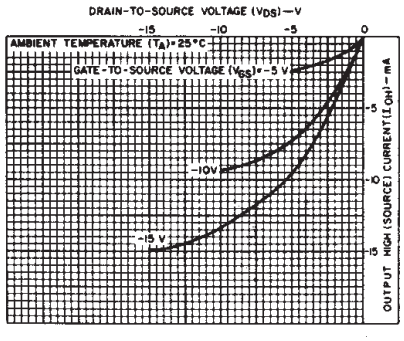


Fig. 9 – Minimum output high (source) current characteristics.

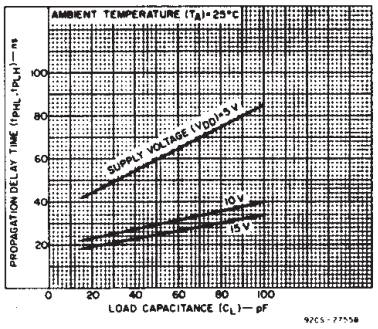


Fig. 10 – Typical propagation delay time vs. load capacitance.

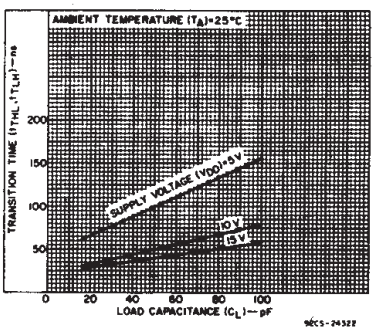


Fig. 11 – Typical transition time vs. load capacitance.

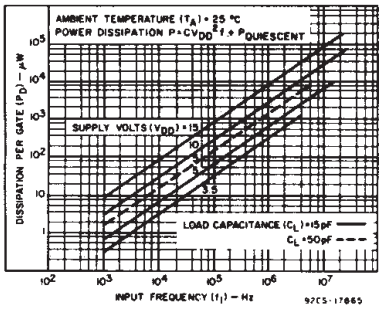


Fig. 12 – Typical power dissipation vs. frequency characteristics.

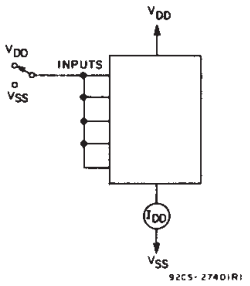


Fig. 13 – Quiescent device current test circuit.

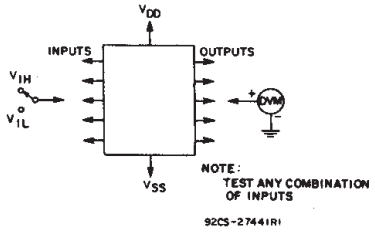


Fig. 14 – Input voltage test circuit.

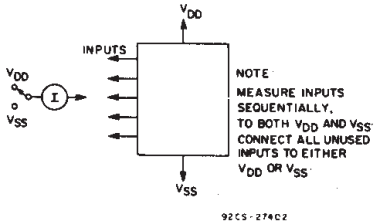
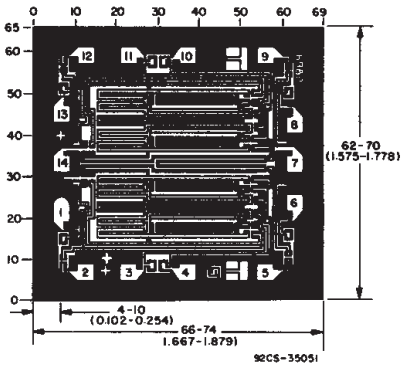


Fig.15 – Input current test circuit.

Chip Dimensions and Pad Layout



CD4011UBH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

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